

VRRM	IF (TC≤135℃)	QC	
650V	39A	86nC	

Applications:

- Switch Mode Power Supplies
- Power Factor Correction
- Motor drive, PV Inverter, Wind Power Station

Features:

- Zero Reverse Recovery Current
- Zero Forward Recovery Voltage
- Positive Temperature Coefficient on VF
- Temperature-independent Switching
- 175°C Operating Junction Temperature

PIN1 PIN2 PIN2 PIN3 CASE PIN3 CASE PIN3 CASE PIN3 CASE PIN3 CASE PIN3 CASE PIN3 CASE

Benefits:

- Replace Bipolar with Unipolar Device
- Reduction of Heat Sink Size
- Parallel Devices Without Thermal Runaway
- Essentially No Switching Losses

Ordering Information

Part Number	Package	Marking	Packing	Qty.
RSS30120K	TO-247-3	RSS30120K	Tube	30 PCS



Maximum Ratings (TJ= 25° C unless otherwise specified)

Symbol	Parameter	Value	Unit	Test Conditions	Note
VRRM	Repetitive Peak Reverse Voltage	1200	V	TC = 25℃	
VRSM	Surge Peak Reverse Voltage	1200	V	TC = 25°C	
VR	DC Blocking Voltage	1200	V	TC = 25°C	
IF	Forward Current	42*21 9.5*2 15/30	A	TC ≤ 25℃ TC ≤ 135℃ TC ≤ 150℃	
IFRM	Repetitive Peak Forward Surge Current	137*2	А	TC = 25℃, tp =8.3ms, Half Sine Wave	
Ptot	Power Dissipation	214*2	W	TC = 25℃	Fig.3
тс	Maximum Case Temperature	150	°C		
TJ,TST G	Operating Junction and Storage Temperature	-55 to175	°C		

Electrical Characteristics (TJ= 25° C unless otherwise specified)

Symbol	Parameter	Тур.	Max.	Unit	Test Conditions	Note	
VF	Forward Voltage	1.55	1.8	V	IF = 15A, TJ = 25℃	Fig 1	
VF	Forward Voltage	2.2	2.5	v	IF = 15A, TJ = 175℃	Fig.1	
IR	Reverse Current	5	20	۸	VR = 1200V, TJ = 25 °C	Fig 2	
IK	Reverse Current	20	200 ^{µA}		VR = 1200V, TJ = 175℃	Fig.2	
		940			VR = 1V, TJ = 25°C, f = 1MHz		
С	Total Capacitance	70	/	pF	VR = 400V, TJ = 25 °C, f = 1MHz	Fig.5	
		57			VR = 800V, TJ = 25 °C, f = 1MHz		
00	Total Capacitive	10	,	~C			
QC	Charge	43	/	nC	VR =800V,	Fig.4	

Thermal Characteristics (TJ= 25°C unless otherwise specified)

Symbol	Parameter	Тур.	Unit	Note
RθJC	Thermal Resistance from Junction to Case	0.7	°C/W	Fig.6



Typical Feature Curve

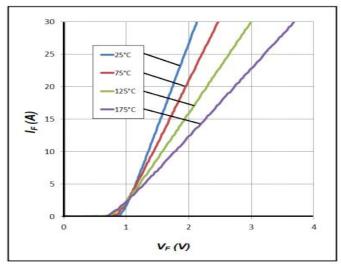


Figure 1. Forward Characteristics

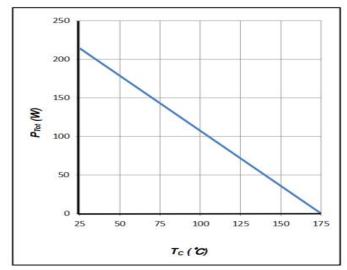


Figure 3. Power Derating

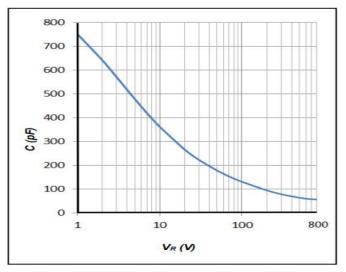


Figure 5. Total Capacitance vs. Reverse Voltage

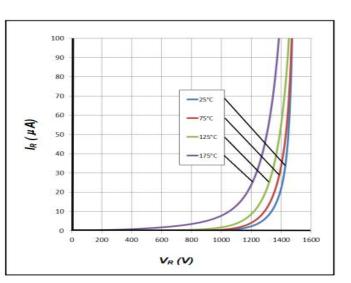


Figure 2. Reverse Characteristics

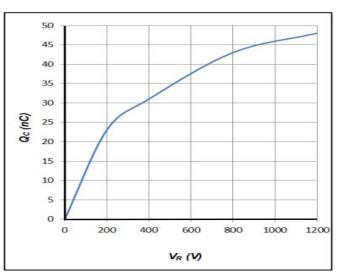


Figure 4. Total Capacitive Charge vs. Reverse Voltage

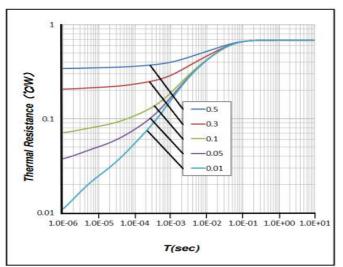
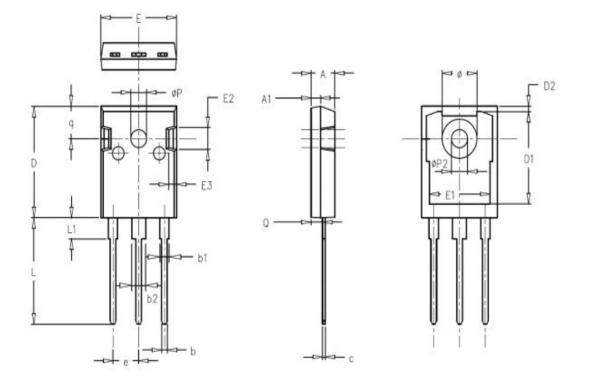


Figure 6. Transient Thermal Impedance



Package outline drawing(TO-247-3 Unit: mm)



SYMBOL	MILLIMETERS		NOTE	CAUDOL	MILLIMETERS			NOTO	
	N ormal	MIN.	MAX.	N OTES	N OTES SYMBOL	Normal	MIN.	MAX.	N OTES
A	4.98	4.68	5.36		øP	3.66	3.45	3.85	
A 1	1.99	1.90	2.10		e	5.44	BSC	;	
Q	2.41	2.30	2.60		q	6.24	5.99	6.58	
с	0.60	0.48	0.72		ØP2	3.45	3.24	3.64	
b	1.20	1.00	1.40		ø	7.14	7.10	7.30	
b1	2.07	1.90	2.30		D1	16.56	16.10	17.10	
b2	3.07	2.90	3.30		D2	0.98	0.80	1.36	
D	21.10	20.80	21.80		E1	13.30	13.00	13.52	
E	15.98	15.38	16.20		E2	5.64	5.10	6.10	
L	20.28	19.50	20.50		E3	2.33	1.90	2.70	
L1	4.01	3.75	4.35						



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